
HD151TS303BST

Spread Spectrum Clock for EMI Solution

REJ03D0216–0101Z
Preliminary
Rev.1.01
Apr.26.2004

Description

The HD151TS303BST is a high-performance Spread Spectrum Clock modulator. It is suitable for low EMI solution.

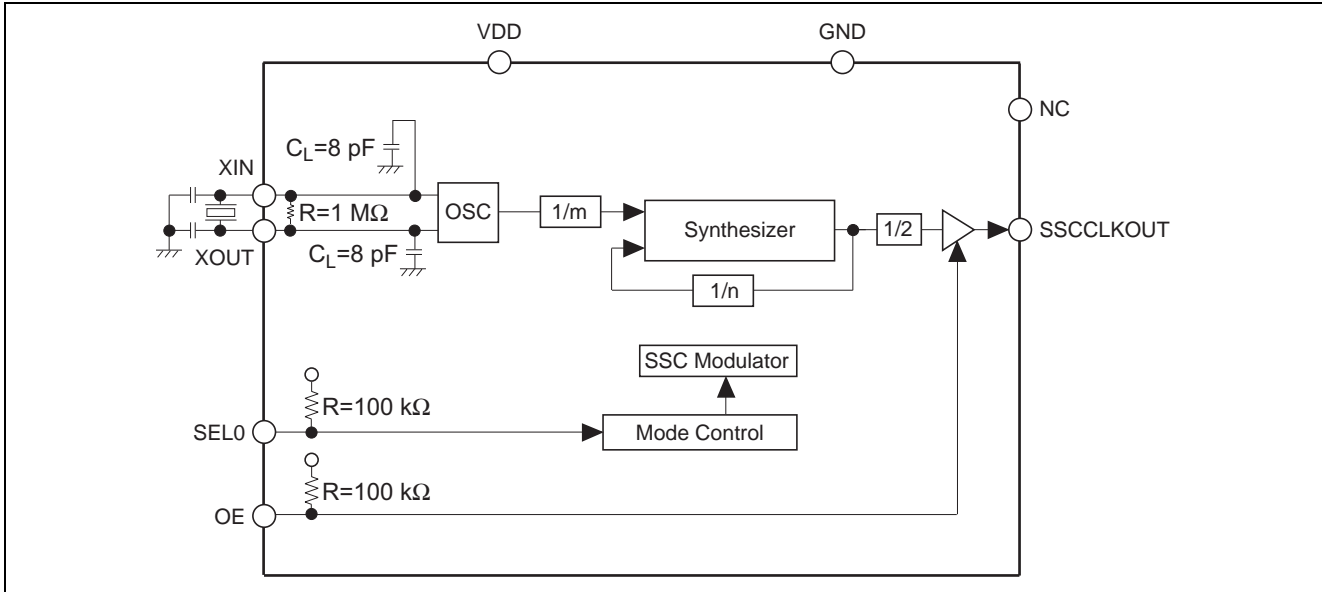
Features

- Supports 10 MHz to 60 MHz operation (Designed for XIN = 48 MHz)
- XIN×1/2 clock out with spread spectrum modulation @3.3 V
- Programmable spread spectrum modulation ($\pm 0.5\%$, $\pm 1.5\%$ central spread modulation.)
- Output Enable function tri-state output.

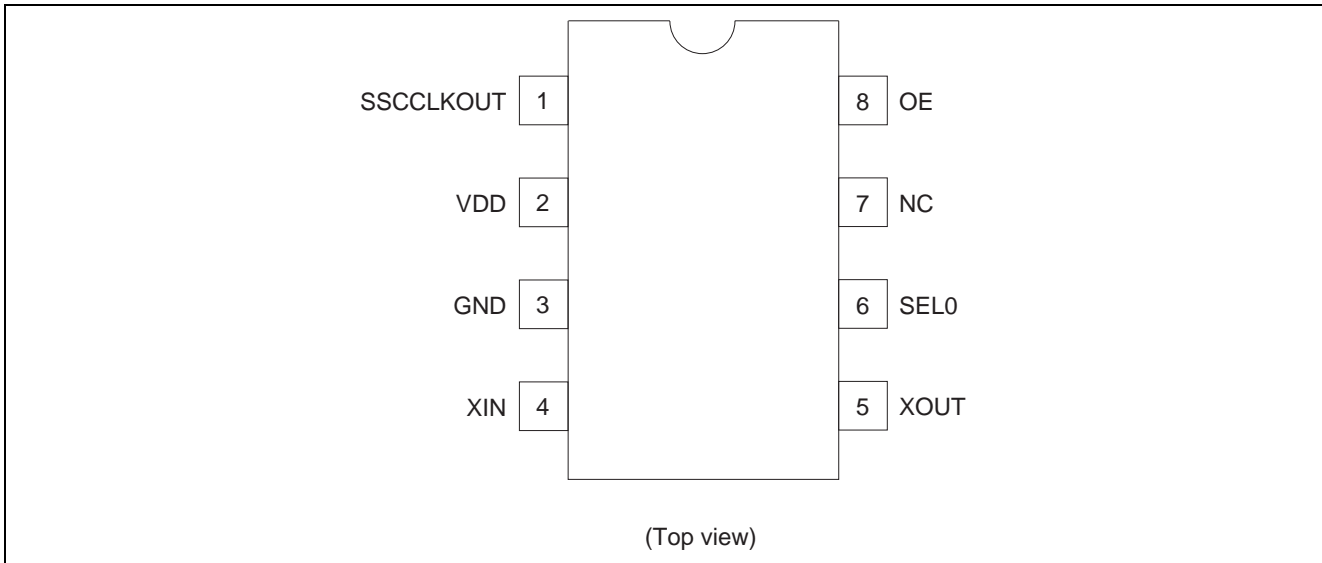
Key Specifications

- Supply voltages : VDD = 3.3 V ± 0.165 V
- Clock output duty cycle = 50 $\pm 5\%$
- Cycle to cycle jitter = ± 250 ps typ.
- Output slew rate = 0.8 V/ns min.

Block Diagram



Pin Arrangement



SSC Function Table

OE: SEL0	Spread Percentage
0 0	Hi-Z
0 1	Hi-Z
1 0	±0.5%
1 1	±1.5%

Note: ±1.5% SSC is selected for default by internal pull-up & down resistors.

Clock Frequency Table

XIN(MHz)	SSCCLKOUT(MHz)
48	24 ^{*1}
24	12 ^{*1}

Notes: 1. With spread spectrum modulation.

Pin Descriptions

Pin name	No.	Type	Description
GND	3	Ground	GND pin
VDD	2	Power	Power supplies pin. Normally 3.3 V.
NC	7	NC	Don't connect any VDD or GND.
SSCCLKOUT	1	Output	Spread spectrum modulated clock output.
XIN	4	Input	Oscillator input.
XOUT	5	Output	Oscillator output.
SEL0	6	Input	SSC mode select pin. LVCMOS level input. Pull-up by internal resistor (100 kΩ).
OE	8	Input	Output Enable. Tri-state output when low. Pull-up by internal resistor (100 kΩ).

Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	VDD	-0.5 to 4.6	V	
Input voltage	V _I	-0.5 to 4.6	V	
Output voltage ^{*1}	V _O	-0.5 to VDD+0.5	V	
Input clamp current	I _{IK}	-50	mA	V _I < 0
Output clamp current	I _{OK}	-50	mA	V _O < 0
Continuous output current	I _O	±50	mA	V _O = 0 to VDD
Maximum power dissipation at Ta = 55°C (in still air)		0.7	W	
Storage temperature	T _{stg}	-65 to +150	°C	

Notes: Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device.

These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

Recommended Operating Conditions

Item	Symbol	Min	Typ	Max	Unit	Conditions
Supply voltage	VDD	3.135	3.3	3.465	V	
DC input signal voltage		-0.3	—	VDD+0.3	V	
High level input voltage	V _{IH}	2.0	—	VDD+0.3	V	
Low level input voltage	V _{IL}	-0.3	—	0.8	V	
Input clock duty cycle		45	50	55	%	

DC Electrical Characteristics
 $T_a = 25^{\circ}\text{C}$, $V_{DD} = 3.3\text{ V}$

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Input low voltage	V_{IL}	—	—	0.8	V	
Input high voltage	V_{IH}	2.0	—	—	V	
Input current	I_I	—	—	± 10	μA	$V_I = 0\text{ V}$ or 3.465 V , $V_{DD} = 3.465\text{ V}$, XIN pin
		—	—	± 100		$V_I = 0\text{ V}$ or 3.465 V , $V_{DD} = 3.465\text{ V}$, SEL0, OE pins
Input slew rate		1	—	4	V/ns	20% – 80%
Input capacitance	C_I	—	—	4	pF	SEL0, OE
Load capacitance* ¹	C_L	—	4	—	pF	Between Pin XIN and XOUT
Operating current		—	7	—	mA	XIN = 24 MHz, $C_L = 0\text{ pF}$, $V_{DD} = 3.3\text{ V}$

Note: 1. Pin XIN and XOUT each has an 8 pF capacitance. When used with a crystal, the two capacitors combined load the crystal with 4 pF.
If driving XIN with a Reference clock signal, the load capacitance will be 8pF (typical).

DC Electrical Characteristics / SSC Clock Output
 $T_a = 25^{\circ}\text{C}$, $V_{DD} = 3.3\text{ V}$

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Output voltage	V_{OH}	3.1	—	—	V	$I_{OH} = -1\text{ mA}$, $V_{DD} = 3.3\text{ V}$
	V_{OL}	—	—	50	mV	$I_{OL} = 1\text{ mA}$, $V_{DD} = 3.3\text{ V}$
Output current	I_{OH}	—	-30	—	mA	$V_{OH} = 1.5\text{ V}$
	I_{OL}	—	30	—		$V_{OL} = 1.5\text{ V}$

AC Electrical Characteristics / SSC Clock Output [Reference Value]

Ta = 25°C, VDD = 3.3 V, CL = 15 pF

Item	Symbol	Min	Typ	Max	Unit	Test Conditions	Notes
Cycle to cycle jitter ^{*1,2}	t _{CCS}	—	250	300		SSCCLKOUT, 24 MHz	SSC= ±1.5% SEL0 = 1 Fig1
Output frequency ^{*1,2}		23.4	—	24.6		SSCCLKOUT, XIN = 48 MHz	SSC= ±1.5% SEL0 = 1
Slew rate ^{*1}	t _{SL}	0.8	—	—	V/ns	@48 MHz	0.4 V to 2.4 V
Clock duty cycle ^{*1}		45	50	55	%		
Output impedance ^{*1}		—	40	—	Ω		
Spread spectrum modulation frequency ^{*1}		—	33	—	KHz	@24 MHz SSCCLKOUT	
Input clock frequency		10	—	60	MHz		
Stabilization time ^{*1,3}		—	—	2	ms		
Output Enable/Disable time ^{*1,4}	t _{PZ}	—	—	100	ns		

- Notes:
- Parameters are target of design. Not 100% tested in production.
 - Cycle to cycle jitter and output frequency are included spread spectrum modulation.
 - Stabilization time is the time required for the integrated circuit to obtain phase lock of its input signal after power up.
 - Output Enable/Disable time is the time required for the integrated circuit to obtain output signal after the OE pin input.

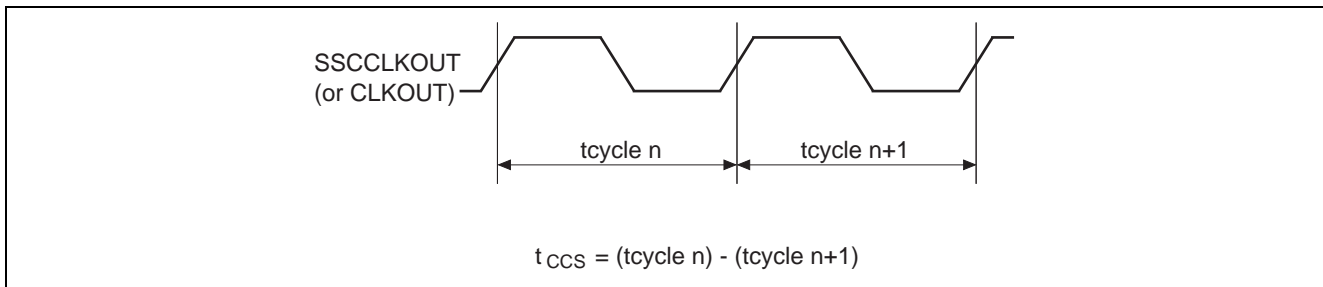


Figure 1 Cycle to cycle jitter

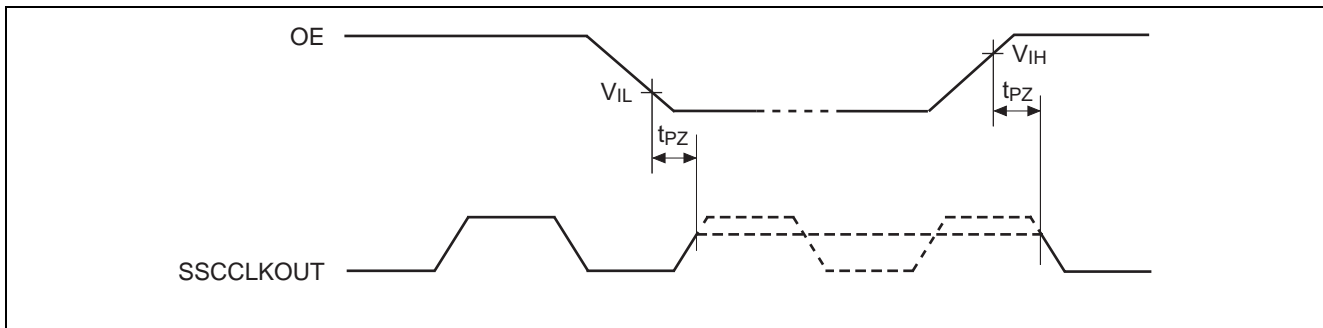


Figure 2 Output Enable/Disable time

Application Information

1. Recommended Circuit Configuration

The power supply circuit of the optimal performance on the application of a system should refer to Fig. 3.

VDD decoupling is important to both reduce Jitter and EMI radiation.

The C1 decoupling capacitor should be placed as close to the VDD pin as possible, otherwise the increased trace inductance will negate its decoupling capability.

The C2 decoupling capacitor shown should be a tantalum type.

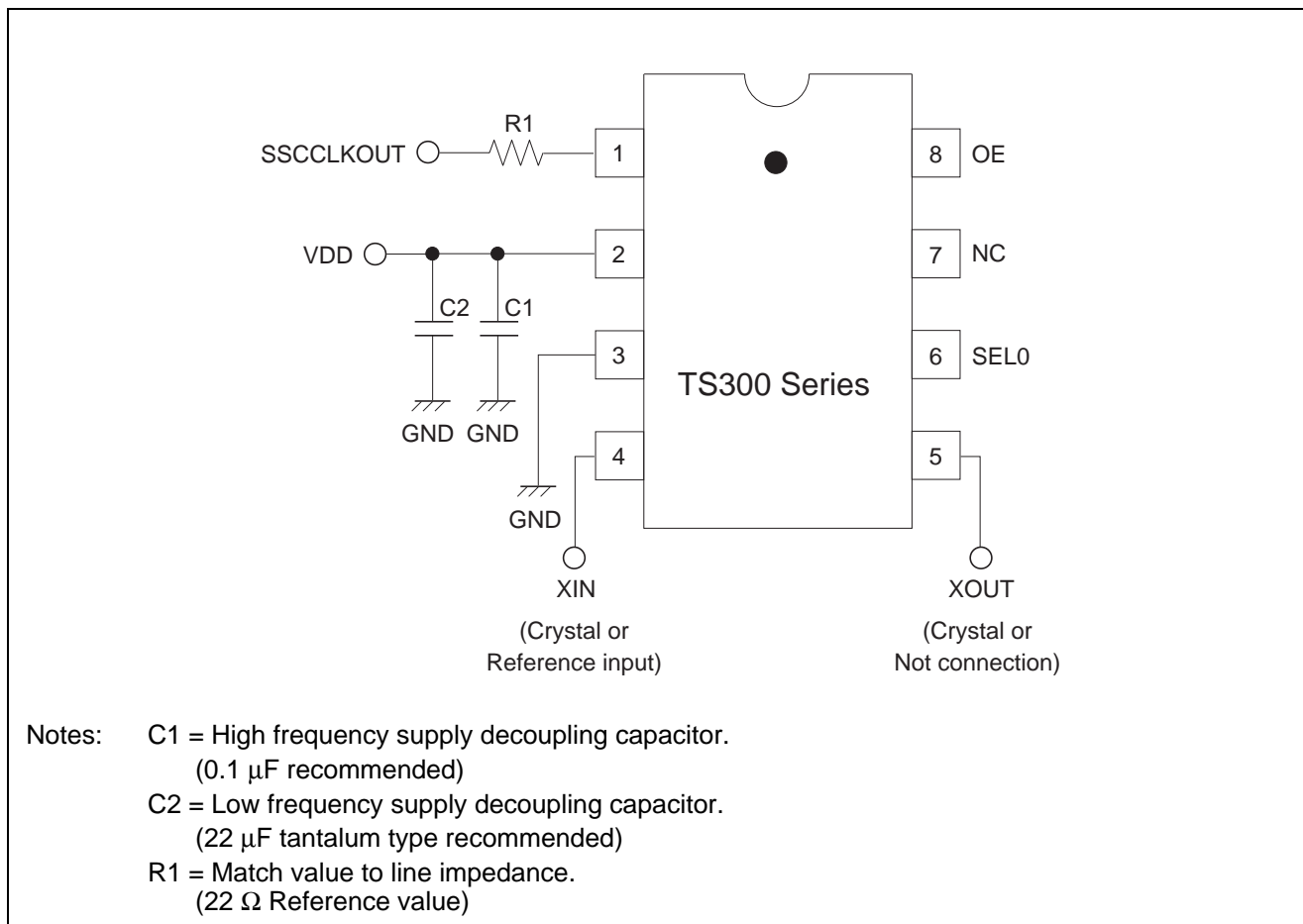


Figure 3 Recommended circuit configuration

3. Example of TS300 EMI Solution IC's Application

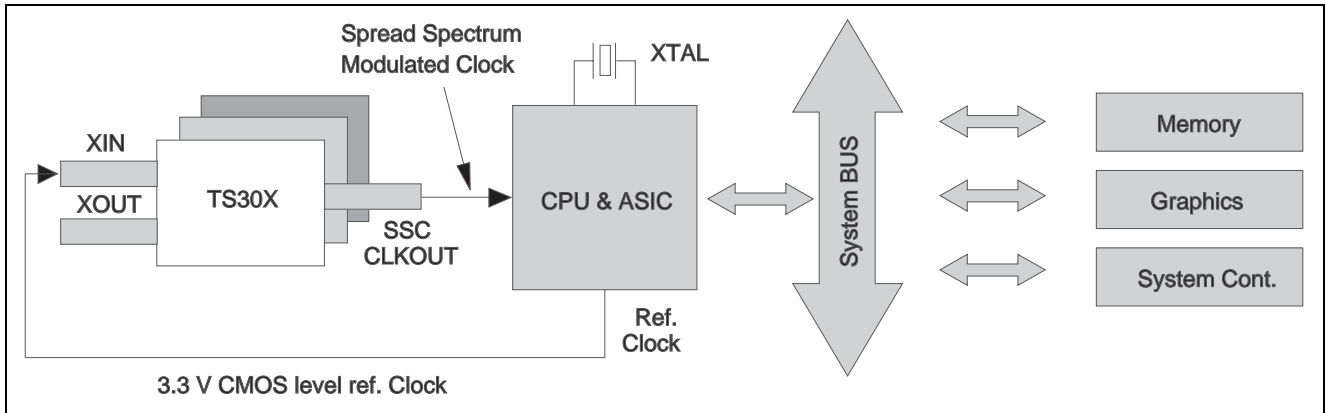


Fig 5 Ref. Clock Input Example

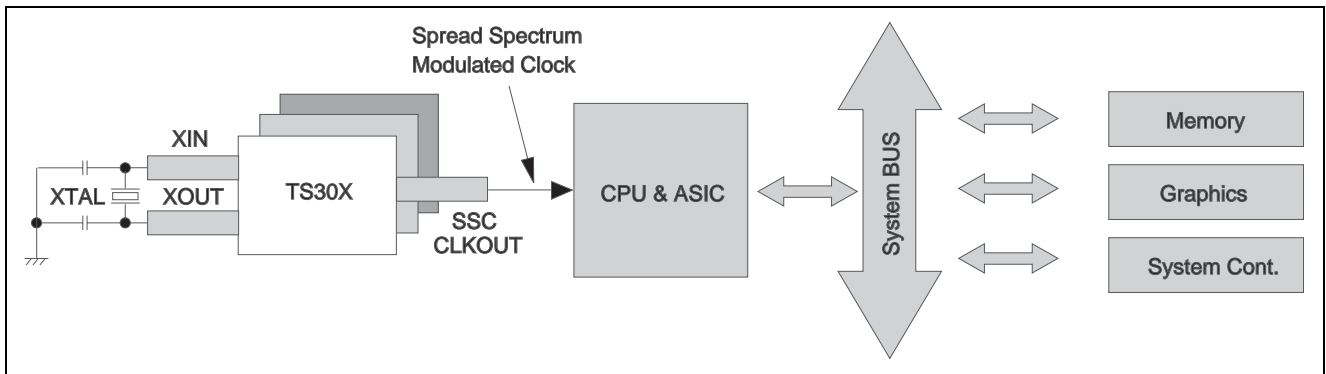


Fig 6 XTAL Ref. Clock Input Example

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